

Band switching diode

Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance

Applications

Band switching in VHF-tuners

Construction

Silicon epitaxial planar



Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
DC Reverse voltage		V_R	35	V
Average rectified current		I_O	100	mA
Power dissipation		P_d	150	MW
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55...+150	$^{\circ}\text{C}$

Maximum Thermal Resistance

$T_j=25^{\circ}\text{C}$

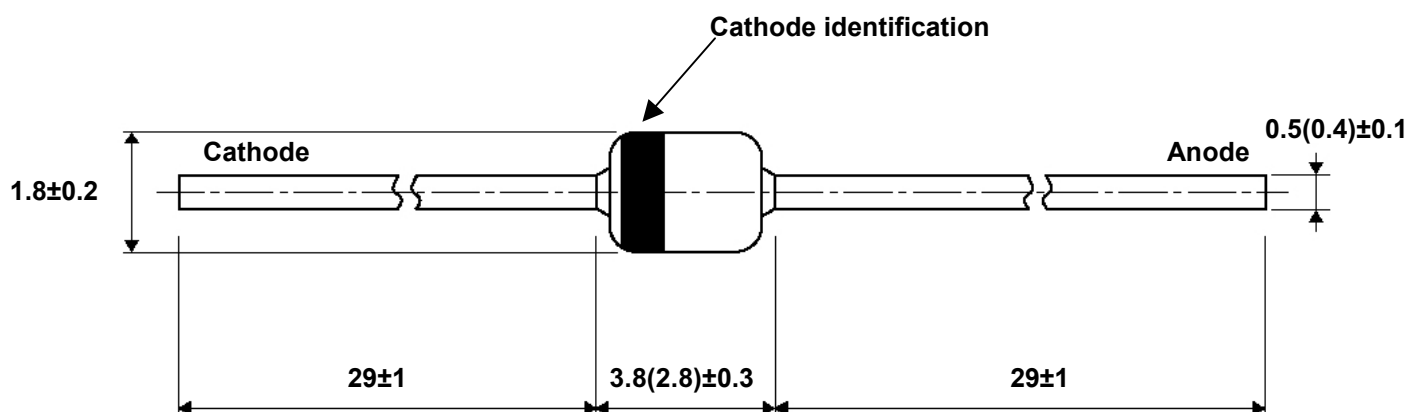
Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=4\text{mm}$, $T_L=\text{constant}$	R_{thJA}	350	K/W

Electrical Characteristics

 $T_J=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=10\text{mA}$	V_F		0.85	1	V
Reverse current	$V_R=20\text{V}$	I_R			100	nA
Breakdown voltage	$I_R=10\mu\text{A}$	B_V	35			V
Terminal capacitance	$f=1\text{MHz}$, $V_R=6\text{V}$	C_t			1.5	pF
Frequency resistance	$f=100\text{MHz}$, $I_F=10\text{mA}$	r_f			0.6	Ω

Dimensions in mm



Standard Glass Case
JEDEC DO - 35 (34)